April 2008



FGA90N33AT 330V, 90A PDP Trench IGBT

Features

- High current capability
- Low saturation voltage: V_{CE(sat)} =1.1V @ I_C = 20A
- High input impedance
- Fast switching
- RoHS compliant

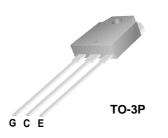
Applications

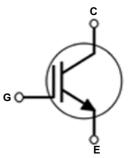
PDP System



General Description

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.





Absolute Maximum Ratings

Symbol	Description		Ratings	Units
V _{CES}	Collector to Emitter Voltage		330	V
V _{GES}	Gate to Emitter Voltage		± 30	V
I _C	Collector Current	@ T _C = 25°C	90	A
I _{C pulse(1)}	Pulsed Collector Current	@ T _C = 25 ^o C	220	A
I _{C pulse(2)}	Pulsed Collector Current	@ T _C = 25°C	330	А
P _D	Maximum Power Dissipation	@ T _C = 25 ^o C	223	W
	Maximum Power Dissipation	@ T _C = 100°C	89	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.56	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Notes:

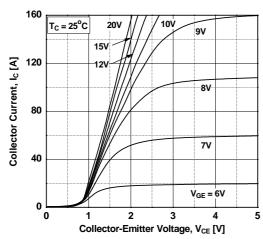
Repetitive test , Pulse width=100usec , Duty=0.1
Half sine wave , D<0.01, Pulse width<5usec

⁽²⁾ Half sine wave , D<0.01, P *I_C pluse limited by max Tj

		Device	Package	Packaging Package Type		Qty per Tube		Max Qty per Box	
		TO-3P	TO-3P Tube		30ea		-		
Electric	al Chai	racteristics of t	he IGBT _{Tc=}	25°C unless otherwise noted					
Symbol		Parameter	Tes	t Conditions	Min.	Тур.	Max.	Units	
Off Charac	teristics								
BV _{CES}	Collector	to Emitter Breakdown V	oltage V _{GE} = 0V,	l _C = 250μA	330	-	-	V	
I _{CES}		Cut-Off Current	-	_s , V _{GE} = 0V	-	-	250	μA	
I _{GES}	G-E Leak	age Current		_S , V _{CE} = 0V	-	-	±400	nA	
								<u> </u>	
On Charac		shold Voltage	lc = 250µA	, V _{CE} = V _{GE}	2.5	4.0	5.5	V	
GL(III)			I _C = 20A, V		-	1.1	1.4	V	
V _{CE(sat)} Colle		Collector to Emitter Saturation Voltage		_{GE} = 15V,	_	1.3	_	V	
	Collector			_{GE} = 15V,	-	1.6	-	V	
		I _C = 90A, V T _C = 125°C	_{GE} = 15V, C	-	1.7	-	V		
Dynamic C	haracteris	tics							
C _{ies}	Input Cap				-	2200	-	pF	
C _{oes}	Output Ca	apacitance	$V_{CE} = 30V_{,}$	$V_{GE} = 0V,$	-	135	-	pF	
C _{res}	Reverse ⁻	Fransfer Capacitance	f = 1MHz		-	100	-	pF	
Switching	Characteri	etice	I		-				
t _{d(on)}		Delay Time				23	-	ns	
t _r	Rise Time			V, $I_{\rm C} = 20$ A,	-	40	-	ns	
t _{d(off)}	Turn-Off	Delay Time	$R_G = 5\Omega, V$ Resistive I	/ _{GE} = 15V, .oad, T _C = 25 ^o C	-	100	-	ns	
t _f	Fall Time	-			-	180	240	ns	
t _{d(on)}		Delay Time			-	20	-	ns	
t _r	Rise Time)	V _{CC} = 200V, I _C = 20A, R _G = 5Ω, V _{GE} = 15V,	$V, I_{\rm C} = 20A,$	-	40	-	ns	
t _{d(off)}	Turn-Off	Delay Time	$R_{G} = 5\Omega, V$ Resistive L	′ _{GE} = 15∨, .oad, T _C = 125°C	-	110	-	ns	
t _f	Fall Time			, <u> </u>	-	250	300	ns	
Q _g	Total Gate	e Charge			-	95	-	nC	
Q _{ge}	Gate to E	mitter Charge		V, I _C = 20A,	-	12	-	nC	
Q _{gc}	Gate to C	ollector Charge	V _{GE} = 15V		-	40	-	nC	

Typical Performance Characteristics







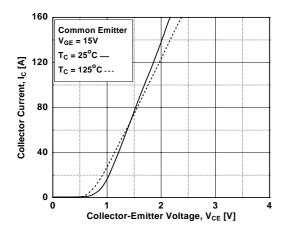


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

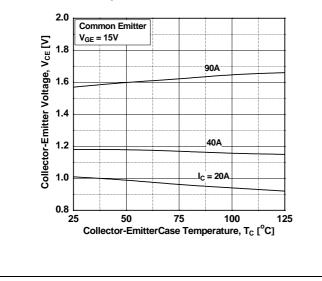


Figure 2. Typical Output Characteristics

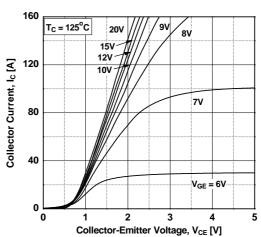


Figure 4. Transfer Characteristics

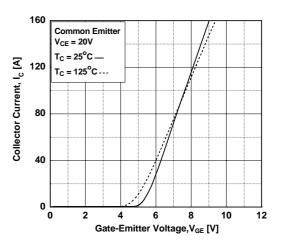
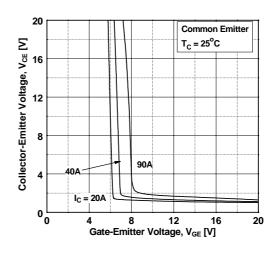


Figure 6. Saturation Voltage vs. V_{GE}



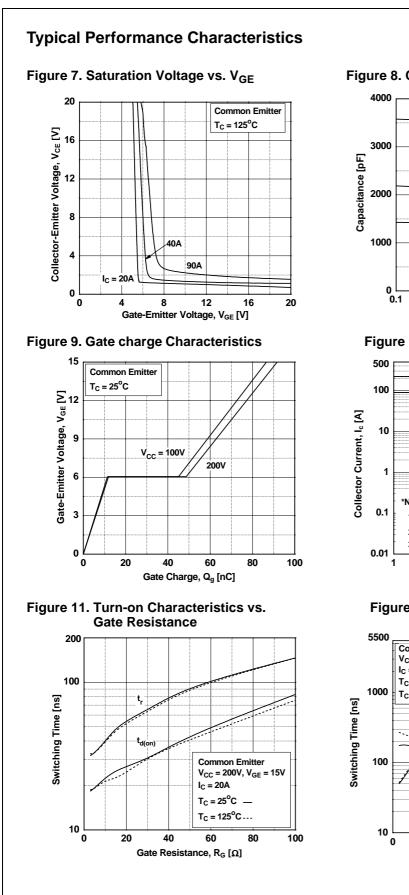


Figure 8. Capacitance Characteristics

Cies

Common Emitter

 $T_C = 25^{\circ}C$

V_{GE} = 0V, f = 1MHz

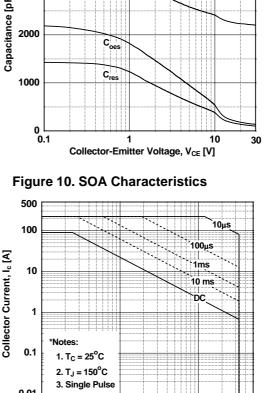


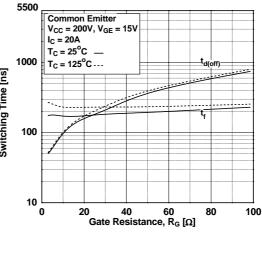
Figure 12. Turn-off Characteristics vs. Gate Resistance

Collector-Emitter Voltage, VCE [V]

100

500

10



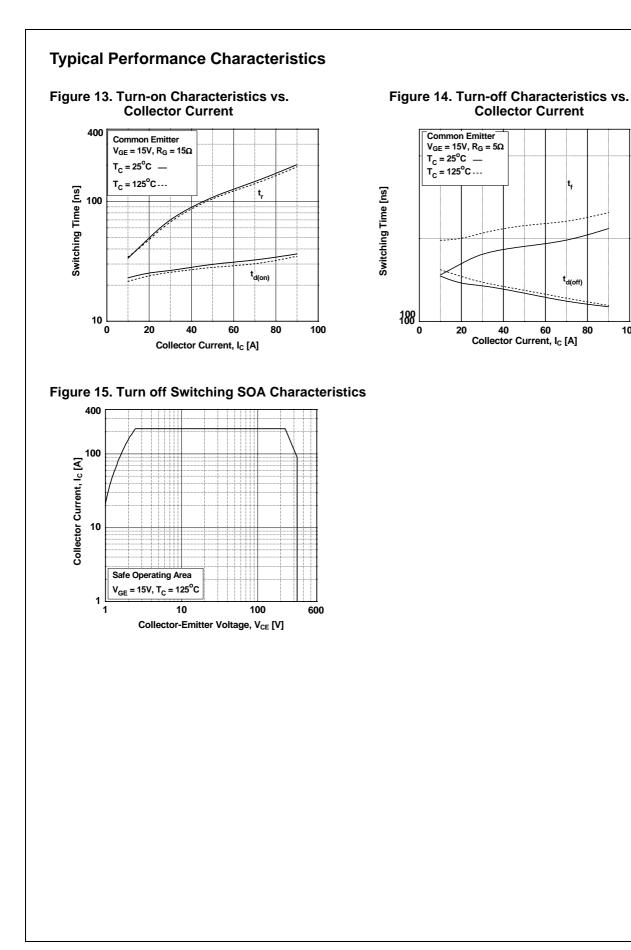
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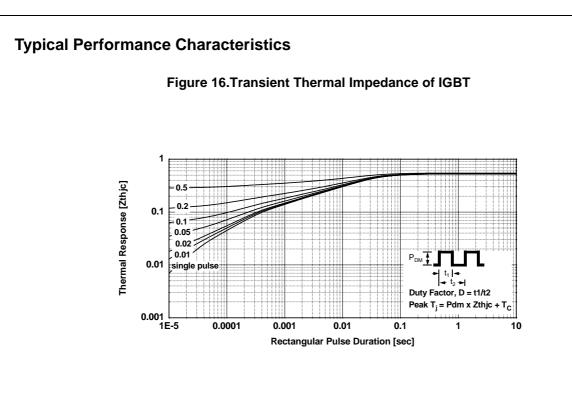
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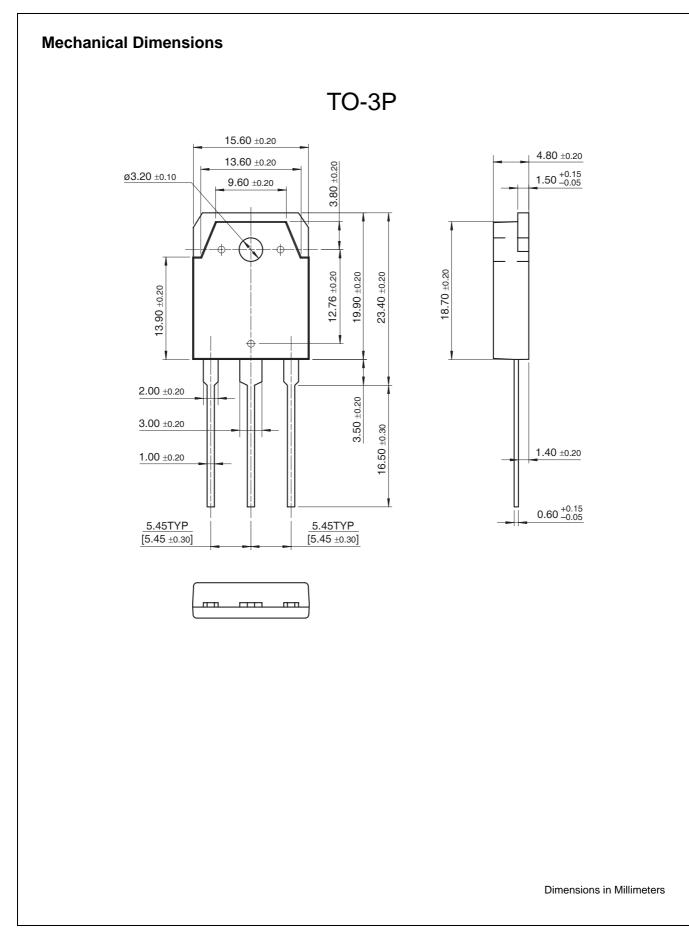
t_{d(off)}

80

100









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